L Number	Hits	Search Text	DB	Time stamp
_	5644	((438/787-788) or (438/694) or (438/700) or (438/702) or (438/976)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 15:31
_	0	(((438/787-788) or (438/694) or (438/700) or (438/702) or (438/976)).CCLS.) and LCD and ((via or trench or opening or plug) same protective same oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 09:40
	5	(((438/787-788) or (438/694) or (438/700) or (438/702) or (438/976)).CCLS.) and LCD and ((via or trench or opening or plug) same oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 09:40
_	59	(((438/787-788) or (438/694) or (438/700) or (438/702) or (438/976)).CCLS.) and ((via or trench or opening or plug) same protective same oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 13:20
_	0	(((438/787-788) or (438/694) or (438/700) or (438/702) or (438/976)).CCLS.) and ((via or trench or opening or plug) same protrrocchengianiective same oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 13:13
_	0	serrocchengiani	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 13:20
-	1923	semiconductor and (via or plug or contact or hole) and gate and LCD and (photoresist or resist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 13:22
_	178	semiconductor and (via or plug or contact or hole) and gate and LCD and ((photoresist or resist) with remov\$4 same wet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21
_	342	semiconductor and (photoresist or resist).ti. and LCD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 13:53
_	135	semiconductor and (photoresist).ti. and LCD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 14:15
-	21	semiconductor and (photoresist with remov\$4 with protect\$4).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 14:19
-	88	semiconductor and (photoresist with overetch)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 14:33
-	384	semiconductor and ((via or contact or plug or hole) with treatment).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 14:55

_	7	(semiconductor and ((via or contact or plug or hole) with treatment).ti.) and LCD	USPAT; US-PGPUB; EPO; JPO;	2003/08/21 14:35
		, , , , , , , , , , , , , , , , , , , ,	DERWENT; IBM_TDB	0000 (00 (01
_	6	(semiconductor and ((via or contact or plug or hole) with treatment).ti.) and UV	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/08/21 14:35
-	0	(semiconductor and ((via or contact or plug or hole) with treatment).ti.) and sacrificial	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/08/21 14:36
-	30	(semiconductor and ((via or contact or plug or hole) with treatment).ti.) and (fill or filling)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/08/21 14:56
-	402	semiconductor and ((trench or via or contact or plug or hole) with treatment).ti.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 14:56
_	7	(semiconductor and ((trench or via or contact or plug or hole) with treatment).ti.) and LCD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 14:56
-	6	(semiconductor and ((trench or via or contact or plug or hole) with treatment).ti.) and UV	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 14:56
_	36	(semiconductor and ((trench or via or contact or plug or hole) with treatment).ti.) and (fill or filling)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 14:56
-	6	<pre>((semiconductor and ((trench or via or contact or plug or hole) with treatment).ti.) and (fill or filling)) not ((semiconductor and ((via or contact or plug or hole) with treatment).ti.) and (fill or filling))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/21 15:11
-	0	semiconductor and (SiN same ILD) and ((photoresist or resist) with strip) and (metal with contact with oxidiz\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 15:13
_	0	semiconductor and (SiN same ILD) and ((photoresist or resist) with strip) and (native with oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 15:13
_	137	semiconductor and (trench or via or contact or hole) and ((photoresist or resist) with strip) and (native with oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 15:14
_	1298	semiconductor and (trench or via or contact or hole) and ((photoresist or resist) with (strip\$4 or remov\$4)) and (native with oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/08/21 15:14
_	40059	(semiconductor and (trench or via or contact or hole) and ((photoresist or resist) with (strip\$4 or remov\$4)) and (native with oxide)) (wet with etch\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/21 15:14

-	71	l '	USPAT;	2003/08/21
		contact or hole) and ((photoresist or resist) with (strip\$4 or remov\$4)) and	US-PGPUB; EPO; JPO;	15:31
		(native with oxide)) and (wet with	DERWENT;	
		etch\$4)	IBM TDB	
-	2390	1 ' '	USPAT;	2003/08/21
			US-PGPUB;	15:31
			EPO; JPO;	
			DERWENT;	
	860	///29/627 640) CCIS) and //matal with	IBM_TDB USPAT;	2003/08/21
-	000	((438/637-640).CCLS.) and ((metal with oxide) or (native with oxide) or	US-PGPUB;	15:32
		(protective with oxide))	EPO; JPO;	13.32
		(Proceeding with one and on	DERWENT;	
			IBM TDB	
-	646	(((438/637-640).CCLS.) and ((metal with	USPAT;	2003/08/21
		oxide) or (native with oxide) or	US-PGPUB;	15:33
	Ï	(protective with oxide))) and (resist or	EPO; JPO;	
		photoresist)	DERWENT;	
1_	5	((((438/637-640).CCLS.) and ((metal with	IBM_TDB USPAT;	2003/08/21
	1	oxide) or (native with oxide) or	US-PGPUB;	15:37
		(protective with oxide))) and (resist or	EPO; JPO;	10.07
1		photoresist)) and LCD	DERWENT;	
			IBM_TDB	
-	325	semiconductor and (MIMS or MUMS)	USPAT;	2003/08/22
			US-PGPUB;	16:59
			EPO; JPO; DERWENT;	
			IBM TDB	
_	248	(semiconductor and (MIMS or MUMS)) and	USPAT;	2003/08/22
		(trench or via or contact or hole)	US-PGPUB;	17:03
			EPO; JPO;	
			DERWENT;	
	13559	gomigandustar and //treat on treatment on	IBM_TDB USPAT;	2003/08/22
-	13339	semiconductor and ((treat or treatment or treated) with (trench or via or contact	US-PGPUB;	17:04
		or hole))	EPO; JPO;	17.01
			DERWENT;	
			IBM_TDB	
-	336		USPAT;	2003/08/22
		or treated) with (trench or via or contact or hole))) and sacrificial	US-PGPUB; EPO; JPO;	17:04
		contact of hole;;; and sacrificial	DERWENT;	
1			IBM TDB	
-	194	((semiconductor and ((treat or treatment	USPAT;	2003/08/22
		or treated) with (trench or via or	US-PGPUB;	17:10
		contact or hole))) and sacrificial) and	EPO; JPO;	
		(photoresist or resist)	DERWENT;	
_	153	rocchegiani	<pre>IBM_TDB USPAT;</pre>	2003/08/22
	100		US-PGPUB;	17:10
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	17	rocchegiani and damascene	USPAT; US-PGPUB;	2003/08/22
			EPO; JPO;	17:11
			DERWENT;	
			IBM TDB	
-	14	("5821169" "5877075" "5882996"	USPĀT	2003/08/22
		"5895253" "6025277" "6057239"		17:13
		"6100184" "6136680" "6153511" "6177364" "6204168" "6211061"		
		"6177364" "6204168" "6211061" "6294457" "6297149").PN.		
_	1	6380073.URPN.	USPAT	2003/08/22
				17:15

-	21	semiconductor and (IC or interconnect)	USPAT;	2003/08/27
		and (via or hole or contact or plug or	US-PGPUB;	10:55
		trench) same (treat\$4 same passivat\$4	EPO; JPO;	
		same ((photoresist or resist) with	DERWENT;	
		(strip\$3 or remov\$4)))	IBM_TDB	
-	154	rocchegiani	USPAT;	2003/08/27
	•		US-PGPUB;	10:56
			EPO; JPO;	
1			DERWENT;	
			IBM_TDB	
-	62	rocchegiani and (via or damascene)	USPAT;	2003/08/27
			US-PGPUB;	11:22
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	12		USPAT	2003/08/27
		"5407855" "5523177" "5561082"		11:13
		"5585673" "5670421" "5731634"		l i
		"5846673" "5969422" "6002174").PN.		
-	14134	(IC or (integrated with circuit)) and	USPAT;	2003/08/27
		((via or trench or contact) same treat\$4)	US-PGPUB;	11:23
			EPO; JPO;	
			DERWENT;	
			IBM_TDB]
-	3003	((IC or (integrated with circuit)) and	USPĀT;	2003/08/27
		((via or trench or contact) same	US-PGPUB;	11:26
		treat\$4)) and ((photoresist or resist)	EPO; JPO;	
	:	with (remove or removing or removal or	DERWENT;	
		strip or stipping or stripped or etch or	IBM TDB	
		etching or etched or ash or ashed or	_	
		ashing))		
_	824		USPAT;	2003/08/27
		((via or trench or contact) same	US-PGPUB;	11:26
		treat\$4)) and ((photoresist or resist)	EPO; JPO;	
		with (remove or removing or removal or	DERWENT;	
		strip or stipping or stripped or etch or	IBM TDB	
		etching or etched or ash or ashed or		
		ashing))) and (UV or (ultraviolet))		1
_	309		USPAT;	2003/08/27
		((via or trench or contact) same	US-PGPUB;	15:36
		treat\$4)) and ((photoresist or resist)	EPO; JPO;	
		with (remove or removing or removal or	DERWENT;	1
		strip or stipping or stripped or etch or	IBM TDB	į.
		etching or etched or ash or ashed or		
		ashing))) and (UV or (ultraviolet))) and		
		(wet with etch\$4)		
-	478	semiconductor and (dielectric adj mask)	USPAT;	2003/08/27
	1		US-PGPUB;	16:29
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	6	(semiconductor and (dielectric adj mask))	USPAT;	2003/08/27
		and (wet adj etch\$4 with (photoresist or	US-PGPUB;	16:33
		resist))	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	3429	(438/694).CCLS.	USPAT;	2003/08/27
	3123		US-PGPUB;	16:33
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	249	((438/694).CCLS.) and trench\$4	USPAT;	2003/08/28
	[1,150,051,100D51, and brononya	US-PGPUB;	09:35
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	5	("5494860" "5814557" "5925933"	USPAT	2003/08/28
	1	"6030895" "6184121").PN.		09:25
L	<u> </u>	1 22222	l	

-	0	semiconductor and (UV with anneal with contact)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/08/28 10:44
			IBM TDB	
-	61	semiconductor and (UV with anneal)	USPAT; US-PGPUB; EPO; JPO;	2003/08/28 10:48
			DERWENT;	
			IBM_TDB	
-	2205		USPAT;	2003/08/28
		resist) with remov\$5).ti.	US-PGPUB; EPO; JPO;	10:49
			DERWENT; IBM TDB	
-	497		USPAT;	2003/08/28
		resist) with remov\$5).ti.) and (trench or	US-PGPUB;	10:49
		via or contact or hole or plug)	EPO; JPO; DERWENT; IBM TDB	
_	51	((semiconductor and ((photoresist or	USPAT;	2003/08/28
		resist) with remov\$5).ti.) and (trench or	US-PGPUB;	12:58
		via or contact or hole or plug)) and (UV	EPO; JPO;	
		or ultraviolet)	DERWENT;	
	82	(438/976).CCLS.	IBM_TDB USPAT;	2003/08/28
	02	(430/9/0).0013.	US-PGPUB;	15:04
			EPO; JPO;	
			DERWENT;	
	700		IBM_TDB	2002/00/20
_	729	semiconductor and (interconnect) and (treatment with (via or contact or trench	USPAT; US-PGPUB;	2003/08/28
		or plug))	EPO; JPO;	13.54
			DERWENT;	
	400		IBM_TDB	2002/00/20
_	423	(semiconductor and (interconnect) and (treatment with (via or contact or trench	USPAT; US-PGPUB;	2003/08/28
		or plug))) and (photoresist or resist)	EPO; JPO;	13.31
		The particular of the particul	DERWENT;	
			IBM_TDB	0000 (00 (00
_	1	((semiconductor and (interconnect) and (treatment with (via or contact or trench	USPAT; US-PGPUB;	2003/08/28
		or plug))) and (photoresist or resist))	EPO; JPO;	13.33
		and ((UV or ultraviolet) same plasma with	DERWENT;	
		(oxidation or oxidize or oxidized))	IBM_TDB	0000 (00 (00
-	1	((semiconductor and (interconnect) and (treatment with (via or contact or trench	USPĀT; US-PGPUB;	2003/08/28
		or plug))) and (photoresist or resist))	EPO; JPO;	13.33
		and ((UV or ultraviolet) same (oxidation	DERWENT;	
		or oxidize or oxidized))	IBM_TDB	2002/00/00
-	223	((semiconductor and (interconnect) and (treatment with (via or contact or trench	USPAT; US-PGPUB;	2003/08/28 15:33
		or plug))) and (photoresist or resist))	EPO; JPO;	10.33
		and ((oxidation or oxidize or oxidized))	DERWENT;	
			IBM_TDB	2002/02/20
-	10	semiconductor and (interconnect) and (UV with treatment with (via or contact or	USPAT; US-PGPUB;	2003/08/28
		trench or plug))	EPO; JPO;	13.33
	Į		DERWENT;	
			IBM_TDB	0000 (00 (00
-	11	semiconductor and (interconnect) and (oxidation with treatment with (via or	USPAT; US-PGPUB;	2003/08/28 15:56
		contact or trench or plug))	EPO; JPO;	13.30
		F-79,1	DERWENT;	
1	_		IBM_TDB	0000 (00 (00
-	0	(LCD or (liquid adj crystal adj display)) and (bus adj line) and (driving with	USPAT; US-PGPUB;	2003/09/03
		transistor with (source or drain)) and	EPO; JPO;	11.10
		polyilicon and (gate with metal)	DERWENT;	
	l		IBM_TDB	

[-	0	(LCD or (liquid adj crystal adj display))	USPAT;	2003/09/03
		and (bus adj line) and (transistor with	US-PGPUB;	11:18
		(source or drain)) and polyilicon and	EPO; JPO;	
		(gate with metal)	DERWENT;	į
			IBM_TDB	İ
-	15	(LCD or (liquid adj crystal adj display))	USPAT;	2003/09/03
		and (bus adj line) and (driving with	US-PGPUB;	11:18
		transistor with (source or drain)) and	EPO; JPO;	
		polysilicon and (gate with metal)	DERWENT;	į į
			IBM_TDB	į į
-	0	((LCD or (liquid adj crystal adj	USPAT;	2003/09/03
		display)) and (bus adj line) and (driving	US-PGPUB;	11:18
		with transistor with (source or drain))	EPO; JPO;	
		and polysilicon and (gate with metal))	DERWENT;	
		and (damascene)	IBM_TDB	
-	14	' '	USPAT;	2003/09/03
		display)) and (bus adj line) and (driving	US-PGPUB;	11:19
		with transistor with (source or drain))	EPO; JPO;	1
		and polysilicon and (gate with metal))	DERWENT;	
		and (trench or via or hole or contact)	IBM_TDB	